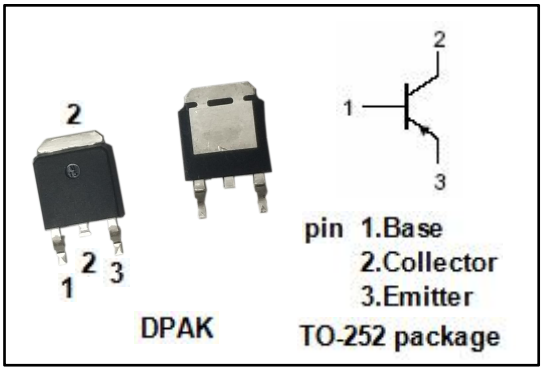
isc Silicon PNP Power Transistors — MJD32C

DESCRIPTION

- DC Current Gain -h_{FE} = 25(Min)@ I_C= -1A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)\ CEO}$= -100V(Min)
- Complement to Type MJD31C
- DPAK for Surface Mount Applications
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

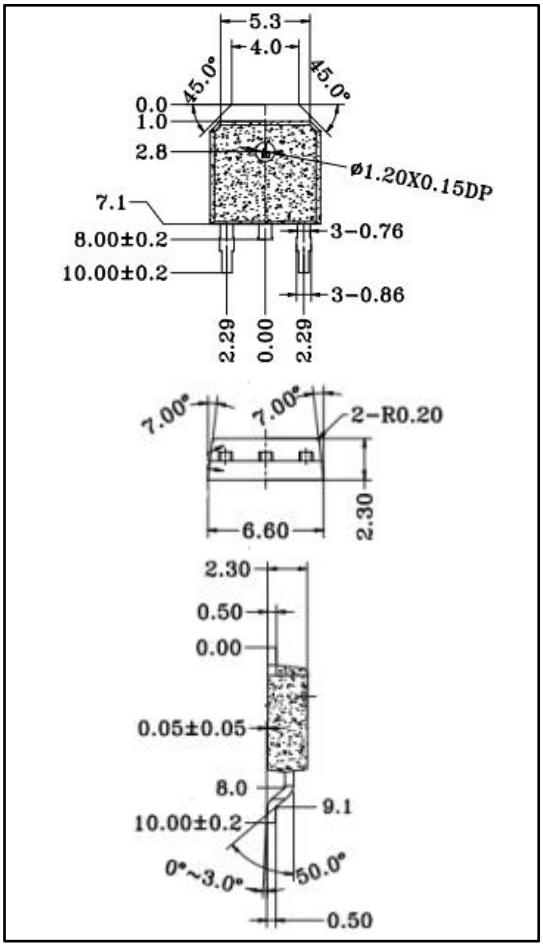


APPLICATIONS

- Designed for use in general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Pulse	-5	A
I_B	Base Current	-1	A
P_C	Collector Power Dissipation T_C=25℃	15	W
	Collector Power Dissipation T_a=25℃	1.56	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Ttemperature Range	-65~150	℃



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	8.3	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA; I_B= 0	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.375A		-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A; V_{CE}= -4V		-1.8	V
I_{CES}	Collector Cutoff Current	V_{CE}= -100V; V_{EB}= 0		-20	uA
I_{CEO}	Collector Cutoff Current	V_{CE}= -60V; I_B= 0		-50	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -4V	25		
h_{FE-2}	DC Current Gain	I_C= -3A; V_{CE}= -4V	10	50	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -10V	3		MHz